

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

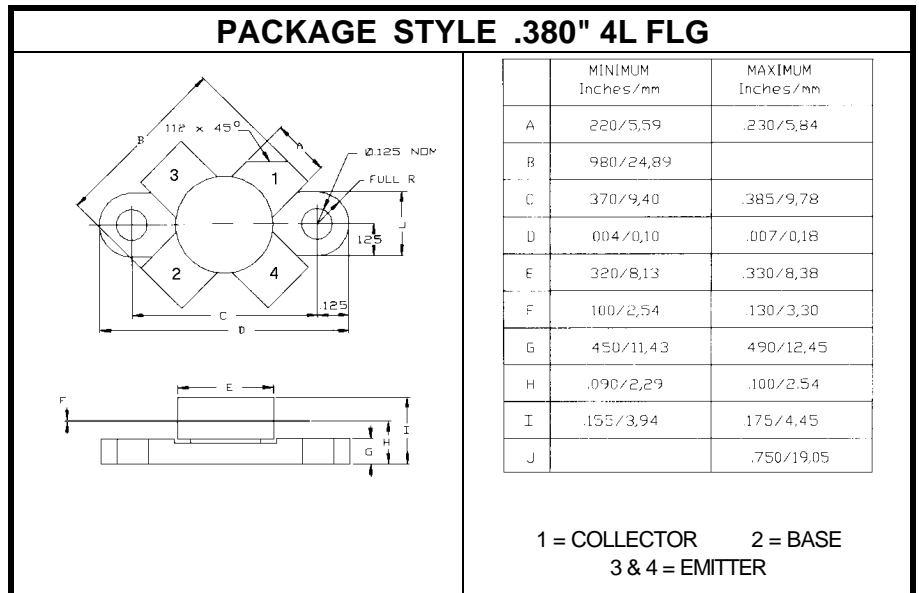
The **ASI S15-28** is Designed for Class AB or C, Common Emitter Linear HF Communications Applications.

FEATURES INCLUDE:

- High Power Gain
- Emitter Ballasting

MAXIMUM RATINGS

I_C	3.0 A
V_{CB}	65 V
P_{DISS}	30 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
q_{JC}	5.8 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 200 mA	65			V
BV_{CEO}	I _C = 200 mA	35			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CBO}	V _{CB} = 30 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 200 mA	10			---
C_{ob}	V _{CB} = 30 V f = 1.0 MHz			35	pF
P_{out}	V _{CE} = 28 V P _{in} = 500 mW fo = 30 MHz	15	---		W
P_g		15	18	---	dB
h_c		---	65		%